

HERMETIC SCHOTTKY POWER RECTIFIER **Low Voltage Drop**

DESCRIPTION: A 45 VOLT, 60 AMP, POWER SCHOTTKY RECTIFIER IN A HERMETIC SHD-2/2B PACKAGE.

MAXIMUM RATINGS

ALL RATINGS ARE @ $T_c = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED.

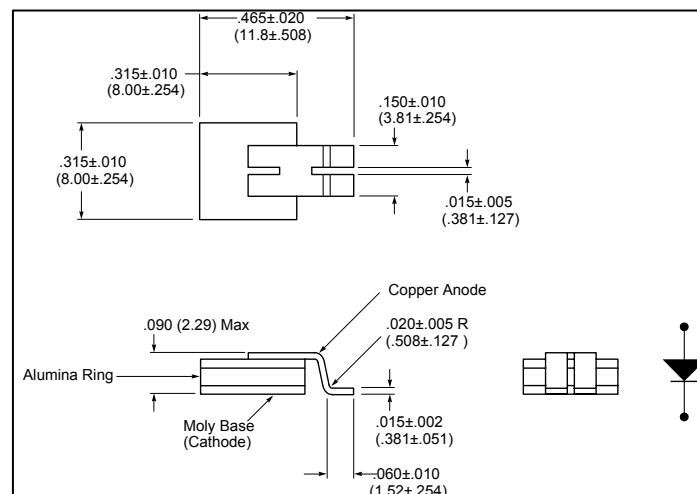
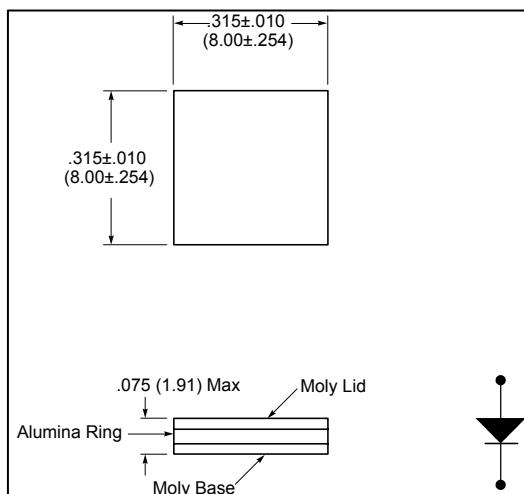
| RATING | SYMBOL | MAX. | UNITS |
|--|-----------------|-----------------|--------------------|
| PEAK INVERSE VOLTAGE | PIV | 45 | Volts |
| MAXIMUM DC OUTPUT CURRENT (With Cathode Maintained @ $T_c = 100^\circ\text{C}$) | I_o | 60 | Amps |
| MAXIMUM NONREPETITIVE FORWARD SURGE CURRENT ($t = 8.3\text{ms}$, Sine) | I_{FSM} | 860 | Amps |
| MAXIMUM JUNCTION CAPACITANCE ($V_r = 5\text{V}$) | C_T | 2400 | pF |
| MAXIMUM THERMAL RESISTANCE (Junction to Mounting Surface, Cathode) | $R_{\theta JC}$ | 0.35 | $^\circ\text{C/W}$ |
| MAXIMUM OPERATING TEMPERATURE RANGE | Top | -65 to + 150 | $^\circ\text{C}$ |
| MAXIMUM STORAGE TEMPERATURE RANGE | T_{stg} | -65 to + 150 | $^\circ\text{C}$ |

ELECTRICAL CHARACTERISTICS

| CHARACTERISTIC | SYMBOL | MAX. | UNITS |
|--|--------|--------------|-------|
| MAXIMUM FORWARD VOLTAGE DROP, Pulsed ($I_f = 60$ Amps) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$ | V_f | 0.62 0.59 | Volts |
| MAXIMUM REVERSE CURRENT (I_r @ 45V PIV) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$ | I_r | 4.5 210 | mA |

SENSITRON

DATA SHEET 1053, REV. C

MECHANICAL DIMENSIONS: In Inches / mmSHD-2SHD-2B**PINOUT TABLE**

| TYPE | PIN 1 (Base) | PIN 2 |
|--|--------------|-------|
| SINGLE RECTIFIER in a Surface Mount Package | CATHODE | ANODE |

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Note: The above V_f characteristics are for die only.

